

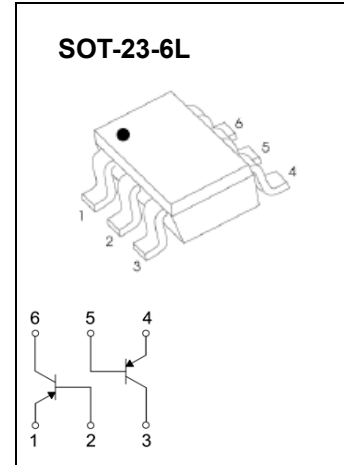
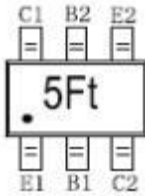
Plastic-Encapsulate Transistors

DUAL TRANSISTOR (PNP+PNP)

FEATURES

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors

MARKING



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

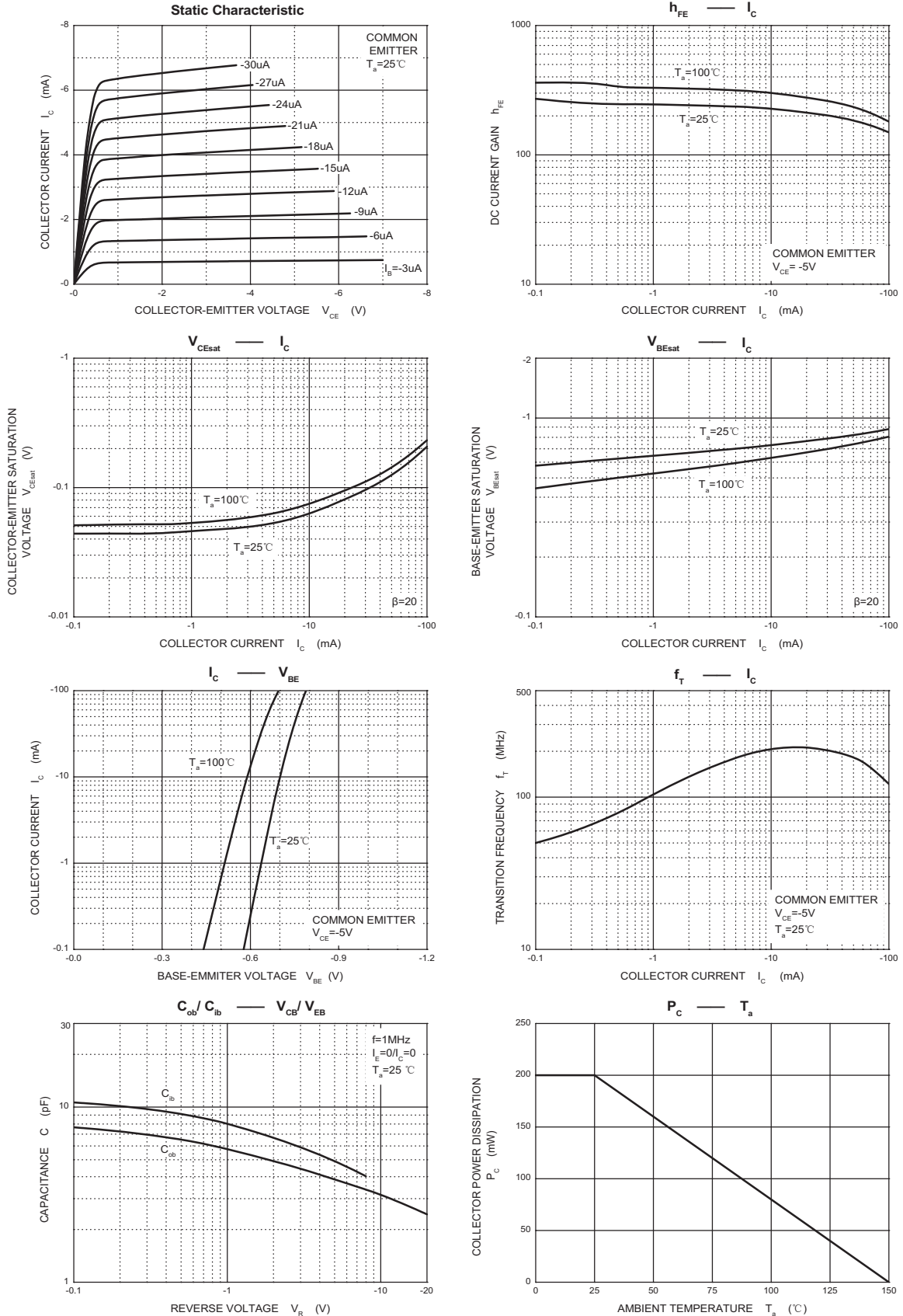
symbol	Parameter	Value	Units
V_{CB0}	Collector- Base Voltage	-80	V
V_{CE0}	Collector-Emitter Voltage	-65	V
V_{EB0}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.1	A
P_C	Collector Power Dissipation	0.2	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	625	$^{\circ}\text{C}/\text{W}$
T_J, T_{STG}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS PNP 540I (Ta=25°C unless otherwise specified)

Parameter	symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-10\mu A, I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-65			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_C=0$	-5			V
Collector cut.off current	I_{CBO}	$V_{CB}=-30V, I_E=0$			-15	nA
Emitter cut.off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-100	nA
DC current gain	h_{FE}	$V_{CE}=-5V, I_C=-2mA$	200		450	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-10mA, I_B=-0.5mA$			-0.1	V
		$I_C=-100mA, I_B=-5mA$ *			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-10mA, I_B=-0.5mA$		0.7		V
output Capacitance	C_{obo}	$V_{CB}=-10V, f=1MHz, I_E=0$			2.5	pF
Current Gain.Bandwidth Product	f_T	$V_{CE}=-5V, I_C=-10mA, f=100MHz$	100			MHz

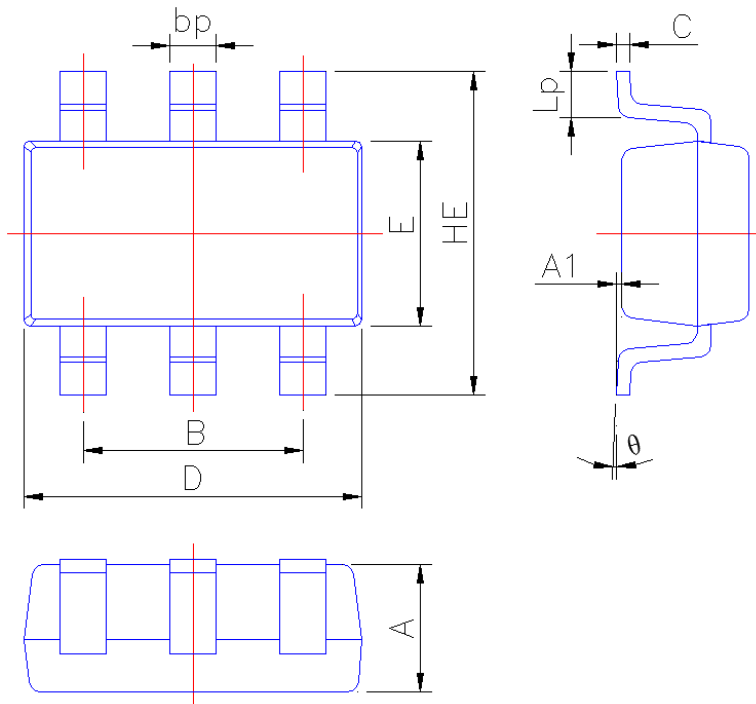
*pulse test: PWs350μS, 0s2% .

Typical Characteristics





SOT-23-6L PACKAGE OUTLINE



Symbol	Dimension in Millimeters	
	Min	Max
A	1.05	1.20
A1	0.010	0.100
B	1.80	2.00
bp	0.35	0.50
C	0.12	0.20
D	2.80	3.00
E	1.50	1.70
HE	2.60	3.00
Lp	0.25	0.55
θ	2°	6°